查询TMD1013-1-431供应商

TOSHIBA MICROWAVE SEMICONDUCTOR

TECHNICAL DATA

## **FEATURES**

lzsc.com

- n HIGH POWER P1dB=33.0dBm at 9.5GHz to 12.0GHz
- n HIGH GAIN G1dB=25.0dB at 9.5GHz to 12.0GHz

捷多邦,专业PCB打样工厂,24小时加急出货

### MICROWAVE POWER MMIC AMPLIFIER TMD1013-1-431

n BROAD BAND INTERNALLY MATCHED

n HERMETICALLY SEALED PACKAGE

# ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	15 001
Flange Temperature	Tf	°C	-30 ~ +80
Storage Temperature	Tstg	°C	-65 ~ +175

# RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

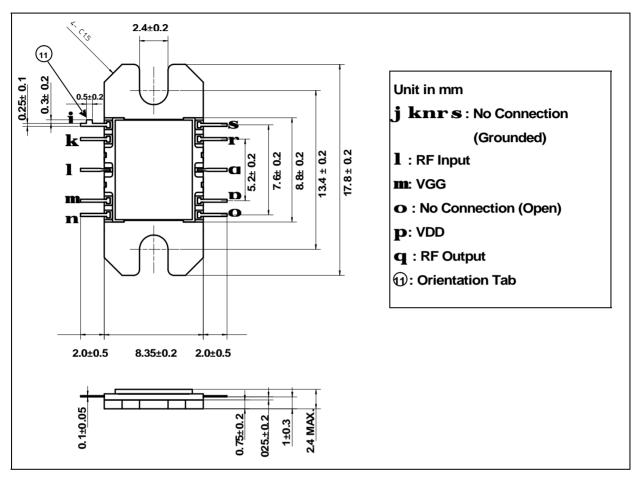
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	31.0	33.0	CON
Compression Point		1 1.30		22	.025	
Power Gain at 1dB Gain	G1dB	VDD= 10V	dB	21.0	25.0	
Compression Point	-170	VGG= -5V				
Gain Flatness	ΔG	f = 9.5 – 12.0GHz	dB			±2.5
Drain Current	IDD		А		1.4	1.8
Power Added Efficiency	<i>h</i> add		%		14	
3 <sup>rd</sup> Order Intermodulation	IM3	2 tone @	dBc	-42	-45	5 20 1
Distortion		Po=19dBm(S.C.L.)		85	145	COM.
		-14	ES.	WWW	.0.5	

**u**The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may results from its use, No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.

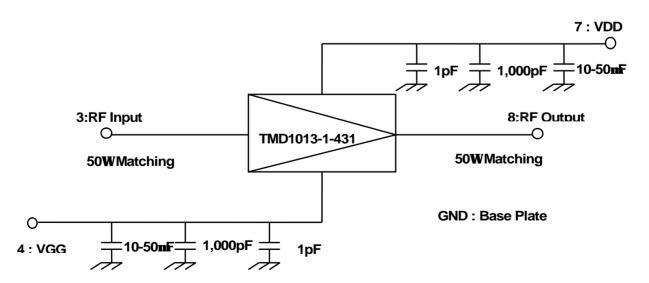
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

TOSHIBA CORPORATION

## **PACKAGE OUTLINE (2-9E1D)**



#### **RECOMMENDED BIAS CONFIGURATION**



#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.